IN THE CLAIMS

Please amend the claims to read as follows:

Listing of Claims

1. (Currently Amended) A method for forming a single crystalline film comprising ~~the steps of~~:

forming an amorphous film on a single crystalline substrate,

forming an opening in the amorphous film and thereby exposing a part of a surface of the substrate through the opening, and

~~introducing~~ directing an atomic beam ~~beams~~, a molecular beam, ~~beams~~ or a chemical ~~beams onto the surface of~~ beam toward the substrate at an incident angle of not more than 40 degrees with respect to the substrate surface to selectively and epitaxially grow a single crystalline film on the exposed surface of the substrate that laterally overgrows the amorphous film ~~under a reduced atmosphere and thereby selectively and epitaxially growing a single crystalline film on the exposed surface of the substrate via the opening, wherein said amorphous film is made of a different material than said substrate and said amorphous film has a dislocation density which is less than or equal to $10^4/cm^2$~~.

2. (Original) A method for forming a single crystalline film as defined in claim 1, wherein the atomic beams, the molecular beams or the chemical beams are introduced at their incident angle of not more than 25 degrees.

3. (Previously presented) A method for forming a single crystalline film as defined in claim 1, wherein atomic beams composed of group V elements in the periodic table, molecular beams or chemical beams containing group V elements in the periodic table are introduced onto the surface of the single crystalline substrate at their incident angle of not more than 40 degrees and atomic beams composed of group III elements in the periodic table, molecular beams or chemical beams containing [III] group III elements in the periodic table are introduced onto the surface of the single crystalline substrate at their any incident angles, and thereby a single crystalline film made of a III-V semiconductor compound is selectively and epitaxially grown on the exposed surface of the substrate.

4. (Original) A method for forming a single crystalline film as defined in claim 3, wherein the atomic beams composed of group V elements in the periodic table, the molecular beams or the chemical beams containing group V elements in the periodic

table are introduced at their incident angle of not more than 25 degrees.

5. (Original) A method for forming a single crystalline film as defined in claim 1, wherein atomic beams composed of group III elements in the periodic table, molecular beams or chemical beams containing group III elements in the periodic table are introduced onto the surface of the single crystalline substrate at their incident angle of not more than 40 degrees and atomic beams composed of group V elements in the periodic table, molecular beams or chemical beams containing group V elements in the periodic table are introduced onto the surface of the single crystalline substrate at their any incident angles, and thereby a single crystalline film made of a III-V semiconductor compound is selectively and epitaxially grown on the exposed surface of the substrate.

6. (Original) A method for forming a single crystalline film as defined in claim 5, wherein the atomic beams composed of group III elements in the periodic table, the molecular beams or the chemical beams containing group III elements in the periodic table are introduced at their incident angle of not more than 25 degrees.

7. (Withdrawn) A method for forming a single crystalline film as defined in claim 1, wherein atomic beams composed of group VI elements in the periodic table, molecular beams or chemical beams containing group VI elements in the periodic table are introduced onto the surface of the single crystalline substrate at their incident angle of not more than 40 degrees and atomic beams composed of group II elements in the periodic table, molecular beams or chemical beams containing group II elements in the periodic table are introduced onto the surface of the single crystalline substrate at their any incident angles, and thereby a single crystalline film made of a II-VI semiconductor compound is selectively and epitaxially grown on the exposed surface of the substrate.

8. (Withdrawn) A method for forming a single crystalline film as defined in claim 7, wherein the atomic beams composed of group VI elements in the periodic table, the molecular beams or the chemical beams containing group VI elements in the periodic table are introduced at their incident angle of not more than 25 degrees.

9. (Withdrawn) A method for forming a single crystalline film as defined in claim 1, wherein atomic beams composed of

group II elements in the periodic table, molecular beams or chemical beams containing group II elements in the periodic table are introduced onto the surface of the single crystalline substrate at their incident angle of not more than 40 degrees and atomic beams composed of group VI elements in the periodic table, molecular beams or chemical beams containing group VI elements in the periodic table are introduced onto the surface of the single crystalline substrate at their any incident angles, and thereby a single crystalline film made of a II-VI semiconductor compound is selectively and epitaxially grown on the exposed surface of the substrate.

10. (Withdrawn) A method for forming a single crystalline film as defined in claim 9, wherein the atomic beams composed of group II elements in the periodic table, the molecular beams or the chemical beams containing group II elements in the periodic table are introduced at their incident angle of not more than 25 degrees.

11. (Original) A method for forming a single crystalline film as defined in any one of claims 1 to 10, wherein the opening has a linear shape and has a width of 0.001 μm to 10 μm.

12. (Original) A method for forming a single crystalline film as defined in any one of claims 1 to 10 wherein the amorphous film is made of an insulating material or a high melting point-metal.

13. (Cancelled).

14. (Currently Amended) A method for forming a single crystalline film as defined in any one of claims 1 to 10 ~~claim 13~~, wherein the single crystalline film is epitaxially grown, from the single crystalline film as a seed which is selectively and epitaxially grown on the exposed surface of the substrate, in a lateral direction parallel to the surface of the substrate on the amorphous film ~~formed on the amorphous film has a disclocation density of not more than $10^{47}/cm^2$~~.

15. (Original) A method for forming a single crystalline film as defined in claim 14, wherein lattice constants of the single crystalline substrate and the single crystalline film are different from each other.

16. (Original) A method for forming a single crystalline film as defined in claim 15, wherein a difference in lattice

constant between the single crystalline substrate and the single crystalline film is 0.1% to 30%.

17. (Previously presented) A method for forming a single crystalline film as defined in claim 1, wherein the single crystalline substrate and the atomic beams, molecular beams or chemical beams are of different materials.

18. (Previously presented) The method of claim 1, wherein:

the single crystalline film and a surface layer of the single crystalline substrate, upon which the single crystalline film is formed, have different molecular structures;

the molecular structure of the single crystalline film is not an alloy of the molecular structure of the surface layer of the single crystalline substrate; and

the molecular structure of the surface layer of the single crystalline substrate is not an alloy of the molecular structure of the single crystalline film.

19. (Withdrawn) The method of claim 18, wherein the single crystalline film is YBCO and the single crystalline substrate is $SrTiO_3$.

20. (Previously presented) The method of claim 1, wherein:

the single crystalline substrate is formed from one of the group of Si, GaAs, ZnSe, $SrTiO_3$, and sapphire; and

the single crystalline film is formed from one of the group of Si, GaAs, $Ga_{1-x}Al_xAs$, ZnSe, ZnS, CdTe, $ZnS_{1-x}Se_x$, and YBCO.

21. (Previously presented) The method of claim 1, wherein:

the single crystalline substrate is formed from one of the group of Si, GaAs, ZnSe, and $SrTiO_3$; and

the single crystalline film is formed from one of the group of Si, GaN, GaAs, $Ga_{1-x}Al_xAs$, ZnSe, ZnS, CdTe, $ZnS_{1-x}Se_x$, and YBCO.

22. (Previously presented) The method of claim 18, wherein:

the single crystalline substrate is formed from one of the group of Si, GaAs, ZnSe, $SrTiO_3$, and sapphire; and

the single crystalline film is formed from one of the group of Si, GaAs, $Ga_{1-x}Al_xAs$, ZnSe, ZnS, CdTe, $ZnS_{1-x}Se_x$, and YBCO.

23. (Previously presented) The method of claim 18 wherein:

the single crystalline substrate is formed from one of the group of Si, GaAs, ZnSe, and $SrTiO_3$; and

the single crystalline film is formed from one of the group of Si, GaN, GaAs, $Ga_{1-x}Al_xAs$, ZnSe, ZnS, CdTe, $ZnS_{1-x}Se_x$, and YBCO.